

TOSHIBA

3SK225

TOSHIBA FIELD EFFECT TRANSISTOR SILICON N CHANNEL DUAL GATE MOS TYPE

3SK225

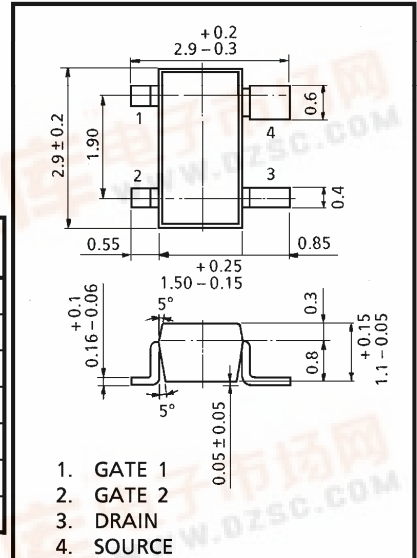
TV TUNER, VHF RF AMPLIFIER APPLICATIONS
FM TUNER APPLICATIONS
TV TUNER, UHF RF AMPLIFIER APPLICATIONS

Unit in mm

- Superior Cross Modulation Performance.
- Low Noise Figure : NF=2.0dB (Typ.)

MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Drain-Source Voltage	V _{DS}	13.5	V
Gate 1-Source Voltage	V _{G1S}	±8	V
Gate 2-Source Voltage	V _{G2S}	±8	V
Drain Current	I _D	30	mA
Drain Power Dissipation	P _D	150	mW
Channel Temperature	T _{ch}	125	°C
Storage Temperature Range	T _{stg}	-55~125	°C



SMQ

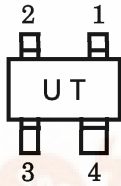
JEDEC —

EIAJ —

TOSHIBA 2-3J1A

Weight : 0.013g

Marking

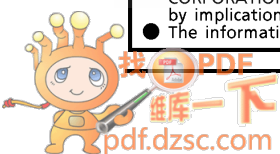


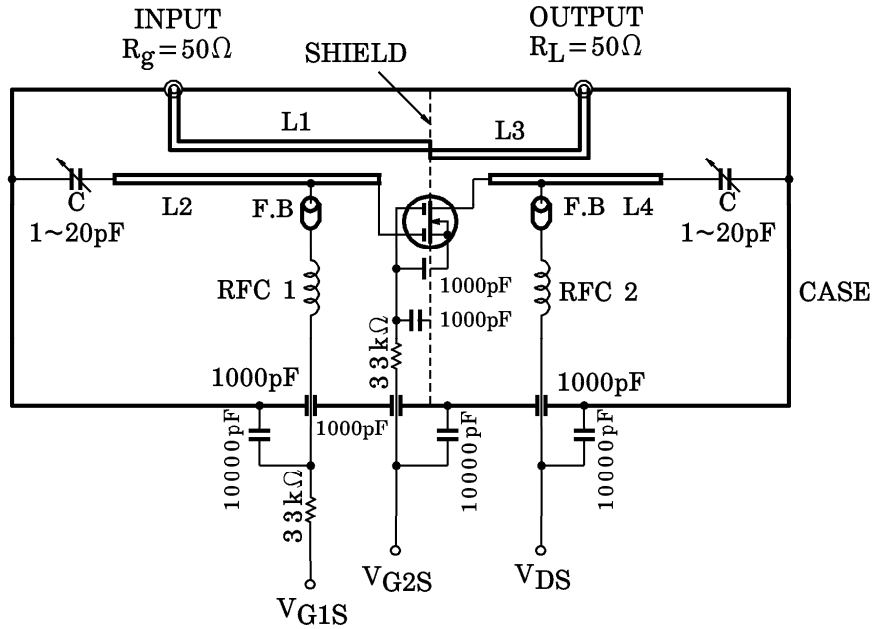
ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Gate 1 Leakage Current	I _{G1SS}	V _{DS} =0, V _{G1S} =±6V, V _{G2S} =0	—	—	±50	nA
Gate 2 Leakage Current	I _{G2SS}	V _{DS} =0, V _{G1S} =0, V _{G2S} =±6V	—	—	±50	nA
Drain-Source Voltage	V (BR) DSX	V _{G1S} =-4V, V _{G2S} =-4V, I _D =100μA	13.5	—	—	V
Drain Current	I _{DSS}	V _{DS} =6V, V _{G1S} =0, V _{G2S} =4.5V	0	—	0.1	mA
Gate 1-Source Cut-off Voltage	V _{G1S} (OFF)	V _{DS} =6V, V _{G2S} =4.5V, I _D =100μA	0	—	1.0	V
Gate 2-Source Cut-off Voltage	V _{G2S} (OFF)	V _{DS} =6V, V _{G1S} =4V, I _D =100μA	0.5	1.0	1.5	V
Forward Transfer Admittance	Y _{fs}	V _{DS} =6V, V _{G2S} =4.5V, I _D =10mA, f=1kHz	—	21	—	mS
Input Capacitance	C _{iss}	V _{DS} =6V, V _{G2S} =4.5V, I _D =10mA, f=1MHz	—	3.4	4.4	pF
Reverse Transfer Capacitance	C _{rss}	V _{DS} =6V, V _{G2S} =4.5V, I _D =10mA, f=1MHz	—	0.020	0.05	pF
Power Gain	G _{ps}	V _{DS} =6V, V _{G2S} =4.5V, I _D =10mA, f=500MHz (Fig.1)	19	22	—	dB
Noise Figure	NF	V _{DS} =6V, V _{G2S} =4.5V, I _D =10mA, f=500MHz (Fig.1)	—	2.0	3.5	dB

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- L1 L4 : ϕ 0.8mm SILVER PLATED COPPER WIRE
- C : AIR TRIMMER TTA25A200A (MURATA MFG. Co., Ltd.)
- RFC 1 : ϕ 0.35mm COPPER WIRE 3mm ID, 7T
- RFC 2 : ϕ 0.35mm COPPER WIRE 3mm ID, 10T

Fig.1 500MHz, G_{ps} , NF TEST CIRCUIT

